

ULTRA HIGH SPEED SWITCHING APPLICATION.

FEATURES

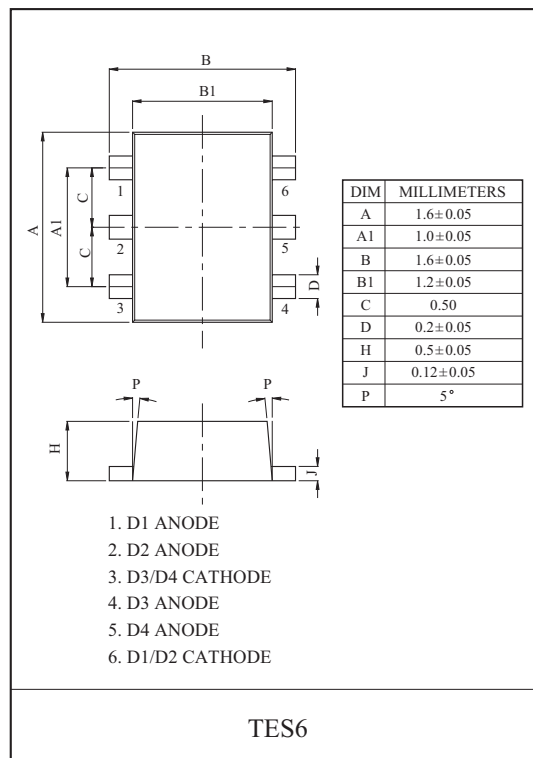
- Low forward voltage. $V_F = 0.9V(\text{Typ.})$
- Fast reverse recovery time. $t_{rr} = 1.6ns(\text{Typ.})$
- Small total capacitance. $C_T = 0.9pF(\text{Typ.})$

MAXIMUM RATING (Ta=25 °C)

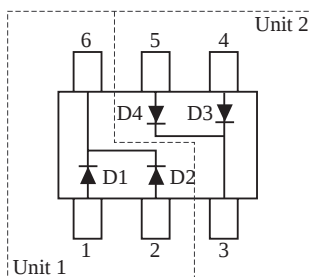
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum (Peak) Forward Current	I_{FM}	300*	mA
Average Forward Current	I_O	100*	mA
Surge Current (10ms)	I_{FSM}	2*	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

* This is Maximum Ratings of single diode (D1 or D2 or D3 or D4).

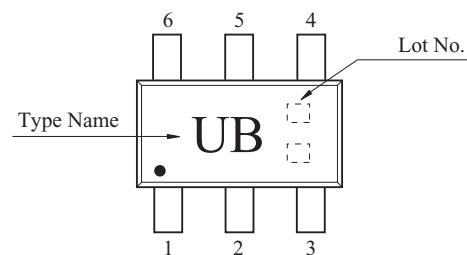
In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.



EQUIVALENT CIRCUIT (TOP VIEW)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_F=1mA$	-	0.60	-	V
	$V_{F(2)}$	$I_F=10mA$	-	0.72	-	
	$V_{F(3)}$	$I_F=100mA$	-	0.90	1.20	
Reverse Current	I_R	$V_R=80V$	-	-	0.5	μA
Total Capacitance	C_T	$V_R=0V, f=1MHz$	-	0.9	3.0	pF
Reverse Recovery Time	t_{rr}	$I_F=10mA$	-	1.6	4.0	ns

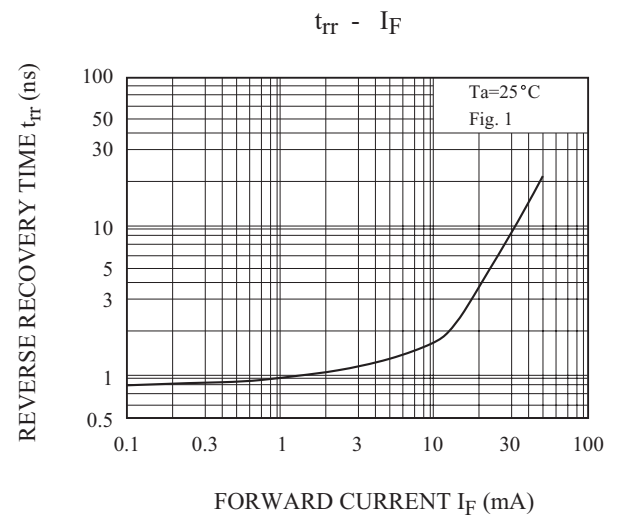
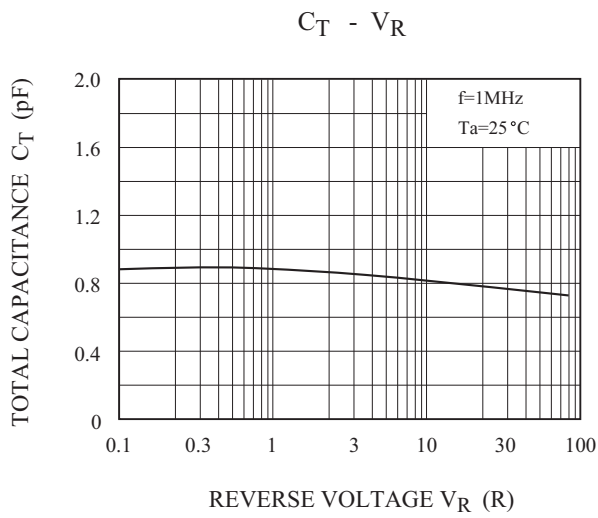
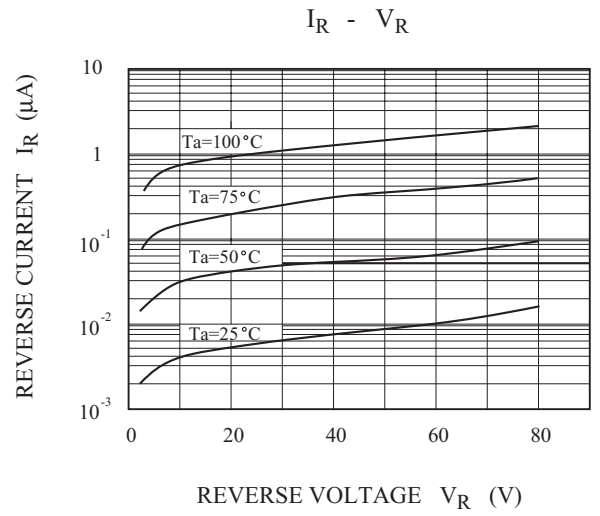
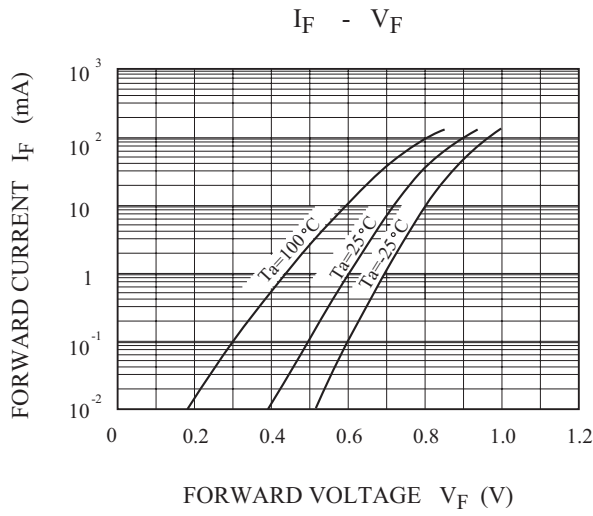


Fig. 1. REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT

